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SEP 20 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hsu et al.

U.S. Serial No: 10/627,000

Filed: July 25, 2003

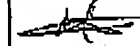
For: METHOD FOR FORMING NON-
VOLATILE MEMORY CELL WITH
LOW-TEMPERATURE-FORMED
DIELECTRIC BETWEEN WORD AND
BIT LINES, AND NON-VOLATILE
MEMORY ARRAY INCLUDING SUCH
MEMORY CELLS

/ Examiner: Schillinger, Laura M.

/ Group Art: 2813

CERTIFICATE OF FACSIMILE TRANSMISSION

I hereby certify that this paper is being facsimile
transmitted to: Commissioner for Patents at fax number 571-
273-8300 on September 20, 2005.



Kenton R. Mullins, Reg. No. 36,331

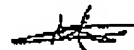
TRANSMITTAL

Sir:

Submitted herewith are (9 pages including this Transmittal):

- (1) Amendment; and
- (2) Deposit Account Authorization: The Commissioner is hereby authorized to charge any needed fees to deposit account 50-1600.

Respectfully submitted,



Kenton R. Mullins
Attorney for Applicants
Registration No. 36,331

September 20, 2005
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AMENDMENT

Dear Sir:

In response to the Office Action mailed July 20, 2005, Applicants respectfully request that the following amendments be entered in the above-identified patent application:

Listing of the Claims are reflected in the listing of claims, which begins on page 2 of this paper.

Remarks/Arguments begin on page 5 of this paper.